



N-Channel 20-V (D-S) MOSFET

TrenchFET®

MOSFETs

1.5-V Rated



ESD Protected 2000 V

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (mA)
20	5 @ V _{GS} = 4.5 V	200
	7 @ V _{GS} = 2.5 V	175
	9 @ V _{GS} = 1.8 V	150
	10 @ V _{GS} = 1.5 V	50

FEATURES

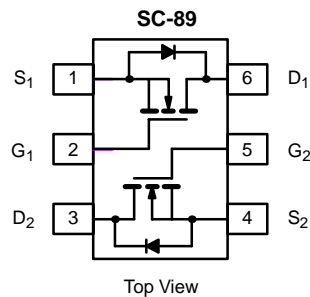
- Low-Side Switching
- Low On-Resistance: 5 Ω
- Low Threshold: 0.9 V (typ)
- Fast Switching Speed: 35 ns (typ)
- 1.5-V Operation
- Gate-Source ESD Protection

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers



Marking Code: L

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V _{DS}	20		V	
Gate-Source Voltage	V _{GS}	±5			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	190	180	mA
		T _A = 85 °C	140	130	
Pulsed Drain Current ^b	I _{DM}	650			
Continuous Source Current (diode conduction)	I _S	450	380		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	280	250	mW
		T _A = 85 °C	145	130	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C	
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000		V	

Notes

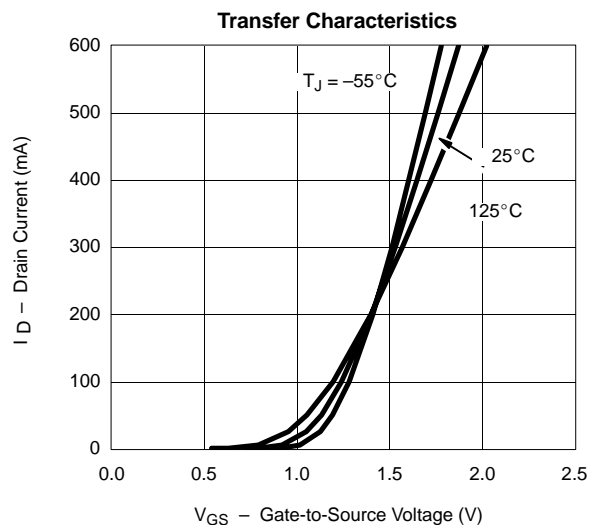
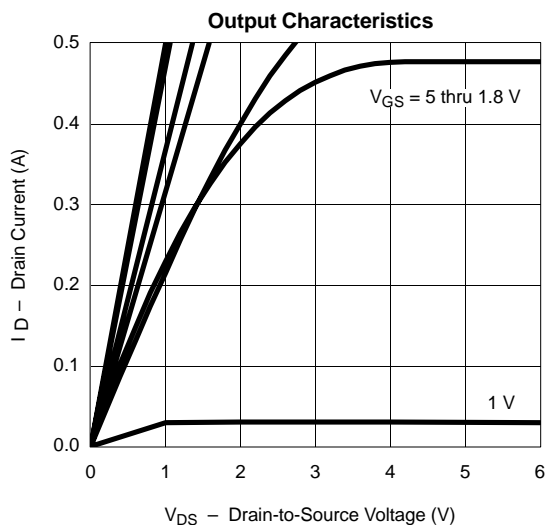
- a. Surface Mounted on FR4 Board.
- b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.40		1.2	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 2.8\ \text{V}$		± 0.5	± 1.0	μA
		$V_{DS} = 0\ \text{V}, V_{GS} = \pm 4.5\ \text{V}$		± 1.0	± 3.0	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}$		1	500	nA
		$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85^\circ\text{C}$			10	μA
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5\ \text{V}, V_{GS} = 4.5\ \text{V}$	250			mA
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\ \text{V}, I_D = 200\ \text{mA}$			5	Ω
		$V_{GS} = 2.5\ \text{V}, I_D = 175\ \text{mA}$			7	
		$V_{GS} = 1.8\ \text{V}, I_D = 150\ \text{mA}$			9	
		$V_{DS} = 1.5\ \text{V}, I_D = 40\ \text{mA}$			10	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\ \text{V}, I_D = 200\ \text{mA}$		0.5		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 150\ \text{mA}, V_{GS} = 0\ \text{V}$			1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 150\ \text{mA}$		750		μC
Gate-Source Charge	Q_{gs}			75		
Gate-Drain Charge	Q_{gd}			225		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\ \text{V}, R_L = 47\ \Omega$ $I_D \cong 200\ \text{mA}, V_{GEN} = 4.5\ \text{V}, R_G = 10\ \Omega$			50	ns
Rise Time	t_r				25	
Turn-Off Delay Time	$t_{d(off)}$				50	
Fall Time	t_f				25	

Notes

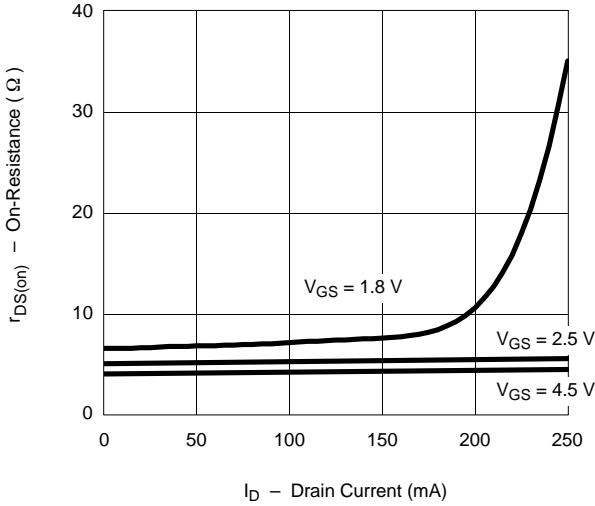
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS NOTED)

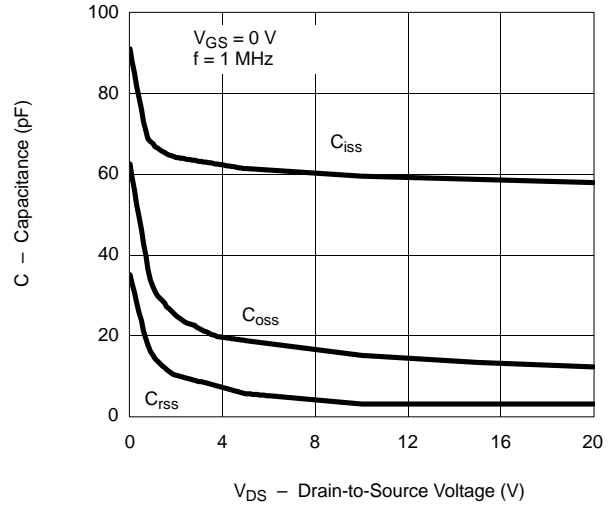


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS NOTED)

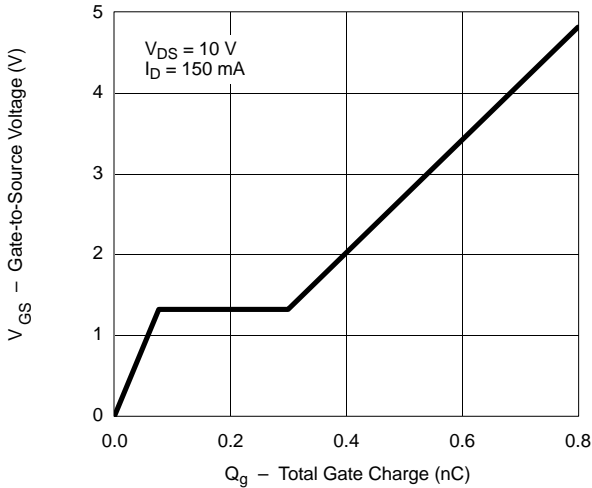
On-Resistance vs. Drain Current



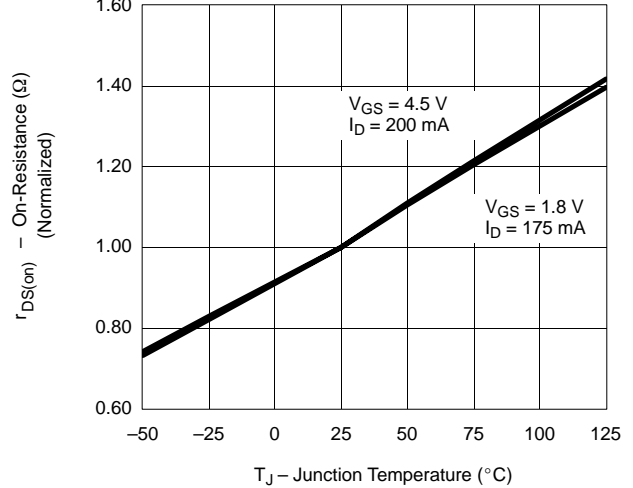
Capacitance



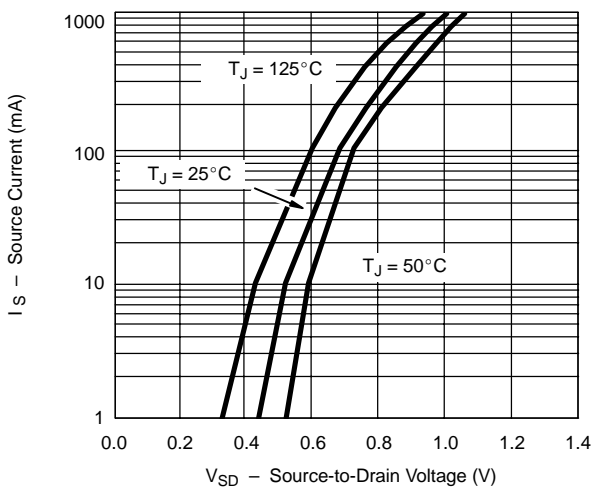
Gate Charge



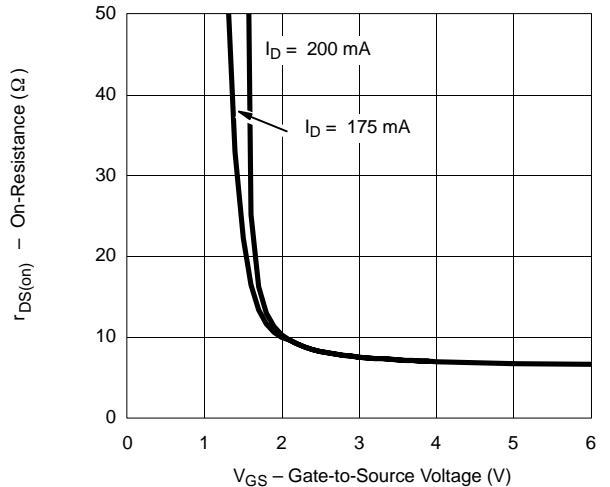
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS NOTED)

